Ballistic vs. Diffusive

Switching in asymmetric spin valve 0 00 Summary

Transport-dependent current-induced switching of symmetric and asymmetric spin valves

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Spin valves Magnetization dynamic

- 2 Ballistic vs. Diffusive
 - Theories Results Co/Cu/Co Py/Cu/Py Co/Cu/Py
- Switching in asymmetric spin valve
 Combined scheme
 Double current pulse



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Spin valves

Definition (Spin valve)

Nanostructure which consists of stacked layers of magnetic and nonmagnetic materials, that alternates its electrical resistance depending of alignment of magnetic layers.



Layers

- Reference (fixed) layer

- Sensing (free) layer

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Magnetization Dynamics

Landau-Lifshitz-Gilbert equation

$$\frac{\mathrm{d}\hat{\mathbf{s}}}{\mathrm{d}t} = -|\gamma_{\mathrm{g}}|\mu_{0}\,\hat{\mathbf{s}}\times\mathbf{H}_{\mathrm{eff}} - \alpha\,\hat{\mathbf{s}}\times\frac{\mathrm{d}\hat{\mathbf{s}}}{\mathrm{d}t} + \frac{|\gamma_{\mathrm{g}}|}{M_{\mathrm{s}}d}\,\boldsymbol{\tau}$$

- $\gamma_{\rm g}$ gyromagnetic ratio, μ_0 vacuum permeability
- ŝ unit vector along the net spin moment
- α the damping parameter
- Ms saturated magnetization
- d3 thickness of the sensing layer

Effective field

$$\mathbf{H}_{\mathrm{eff}} = -H_{\mathrm{ext}} \hat{\mathbf{e}}_{z} - H_{\mathrm{ani}} \left(\hat{\mathbf{s}} \cdot \hat{\mathbf{e}}_{z} \right) \hat{\mathbf{e}}_{z} + \mathbf{H}_{\mathrm{demag}}$$

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Spin-torques

In-plane component

Out-of-plane component

 $m{ au}_{ heta} \propto I \, \hat{f{s}} imes (\hat{f{s}} imes \hat{f{S}})$

 $oldsymbol{ au}_{\phi} \propto I \, \hat{f s} imes \hat{f S}$



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Ballistic transport

J. C.

J. C. Slonczewski Current-driven excitations of magnetic multilayers J. Magn. Magn. Mater. **159**, L1-L7 (1996)

In-plane component

Out-of-plane component

$$\boldsymbol{\tau}_{\theta} = \frac{g\mu_{\mathrm{B}}\boldsymbol{I}}{(1+\alpha^{2})d\boldsymbol{e}}\,\epsilon(\theta,\eta)\,\hat{\boldsymbol{\mathsf{s}}}\times(\hat{\boldsymbol{\mathsf{s}}}\times\hat{\boldsymbol{\mathsf{S}}}) \qquad \boldsymbol{\tau}_{\phi} = -\frac{g\mu_{\mathrm{B}}\alpha\boldsymbol{I}}{(1+\alpha^{2})d\boldsymbol{e}}\,\epsilon(\theta,\eta)\,\hat{\boldsymbol{\mathsf{s}}}\times\hat{\boldsymbol{\mathsf{S}}}$$

Spin torque efficiency function

$$\epsilon(heta,\eta) = \left[-4 + \left(1+\eta
ight)^3 \left(3+\cos heta
ight)/4\eta^{3/2}
ight]^{-1}$$

- η effective Fermi-level polarization factor
- d thickeness of sensing layer
- θ angle between sensing and reference layer magetization

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Diffusive transport

J. Barnaś, A. Fert, M. Gmitra, I. Weymann, V. K. Dugaev From giant magnetoresistance to current-induced switching by spin transfer Phys. Rev. B 72, 024426 (2005)

In-plane component

Out-of-plane component

$$oldsymbol{ au}_{ heta} = a \, l \, \hat{f s} imes (\hat{f s} imes \hat{f S}) \qquad \qquad oldsymbol{ au}_{\phi} = b \, l \, \hat{f s} imes \hat{f S}$$

Angular dependence of spin-tranfer torque

$$\begin{aligned} \mathbf{a} &= \frac{\hbar}{le^2} \left[\operatorname{Re} \{ G_{\min X} \} \left[\cot \theta \left(g_X \cos \varphi + g_Y \sin \varphi \right) - g_Z \right] + \frac{\operatorname{Im} \{ G_{\min X} \}}{\sin \theta} \left(g_X \sin \varphi - g_Y \cos \varphi \right) \right] \\ \mathbf{b} &= -\frac{\hbar}{le^2} \left[\frac{\operatorname{Re} \{ G_{\min X} \}}{\sin \theta} \left(g_X \sin \varphi - g_Y \cos \varphi \right) - \operatorname{Im} \{ G_{\min X} \} \left[\cot \theta \left(g_X \cos \varphi + g_Y \sin \varphi \right) - g_Z \right] \right] \end{aligned}$$

- $\mathbf{g} \equiv (g_x, g_y, g_z)$ spin accumulation (vector in spin-space)
- G_{mix} mixing conductance (interfacial parameter)
- θ angle between sensing and reference layer magetization

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Ballistic regime

Diffusive regime



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Ballistic regime

Diffusive regime



Ballistic vs. Diffusive

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Ballistic regime

Diffusive regime



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Ballistic regime

Diffusive regime



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Diffusive regime



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Diffusive regime



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Ballistic vs. Diffusive

Switching in Co/Cu/Py valve: pulse switching diagram



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Combined current-field switching scheme



Ballistic vs. Diffusive

Switching in asymmetric spin value \circ \circ

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Double rectangular pulse switching scheme

Single rectangular pulse

Symmetric double pulse

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Pulse switching diagrams for Co/Cu/Py



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Summary

• We have compared the torques exerted on a sensing layer of spin valve in dependance of the electron transport regime (Ballistic vs. Diffusive). In the case of asymmetric spin valve have been found significant differencies due to wavy-torque.

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- We have compared the torques exerted on a sensing layer of spin valve in dependance of the electron transport regime (Ballistic vs. Diffusive). In the case of asymmetric spin valve have been found significant differencies due to wavy-torque.
- The dynamical switching diagram of several spin valve structures have been calculated in both, ballistic and diffusive, transport limits. In case of asymmetric spin valve the novel dynamical modes (*out-of-plane precession* and *stable state*) have been found.

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- We have compared the torques exerted on a sensing layer of spin valve in dependance of the electron transport regime (Ballistic vs. Diffusive). In the case of asymmetric spin valve have been found significant differencies due to wavy-torque.
- The dynamical switching diagram of several spin valve structures have been calculated in both, ballistic and diffusive, transport limits. In case of asymmetric spin valve the novel dynamical modes (*out-of-plane precession* and *stable state*) have been found.
- Because of P/AP *bistable* behaviour found in *pulse* diagrams constructed for Co/Cu/Py spin valve, two different efficient switching schemes for asymmetric spin valves have been proposed and examed.

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Thank you for your attention



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